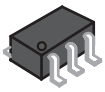
Elektronische Bauelemente

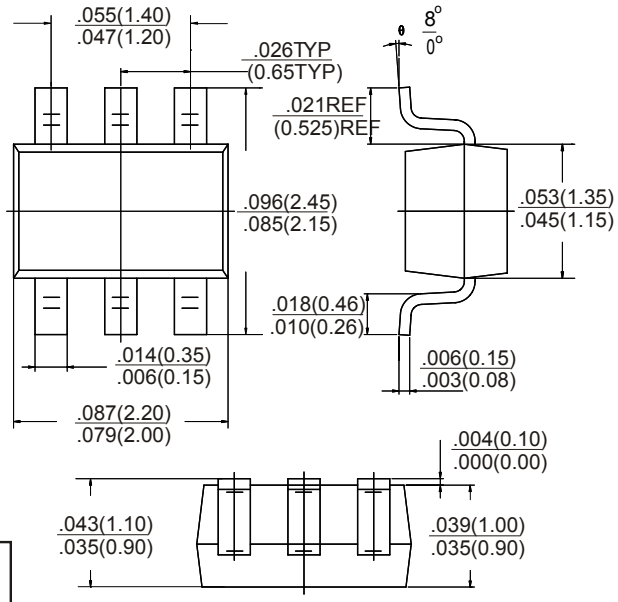
BC857S

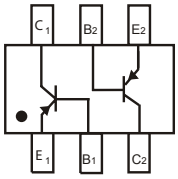
PNP Silicon
Multi-Chip Transistor

RoHS Compliant Product



SOT-363





Dimensions in inches and (millimeters)

* Features

Power dissipation

P_{CM} : 0.3 W (Tamp.= 25°C)

Collector current

I_{CM} : -0.2 A

Collector-base voltage

$V_{(BR)CBO}$: -50 V

Operating & Storage junction Temperature

T_j, T_{stg} : -55°C~ +150°C

Marking : 3C

Electrical Characteristics(Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-10μA, I_E=0	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-10mA, I_B=0	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-30V, I_E=0			-15	nA
DC current gain	h_{FE}	V_{CE}=-5V, I_C=-2mA	125		630	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10mA, I_B=-0.5mA			-0.3	V
	$V_{CE(sat)}$	I_C=-100mA, I_B=-5mA			-0.65	V
Base-emitter voltage	V_{BE}	V_{CE}=-5V, I_C=-2mA	-0.6		-0.75	V
	$V_{BE(1)}$	V_{CE}=-5V, I_C=-10mA			-0.82	V
Transition frequency	f_T	V_{CE}=-5V, I_C=-10mA , f=100MHz		200		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		3.5		pF
Noise figure	NF	V_{CE}=-5V, I_C=-0.2mA F=1kHZ, RS=2KΩ ,BW=200Hz		2.5		dB

Note: 1 Short duration test pulse used to minimize self-heating effect.

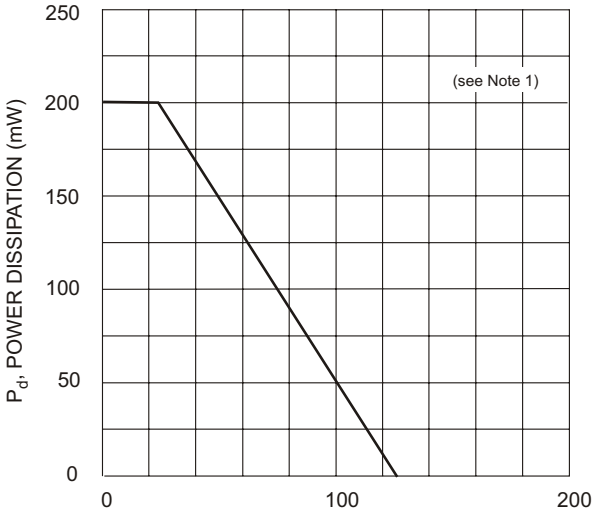


Fig. 1, Power Derating Curve

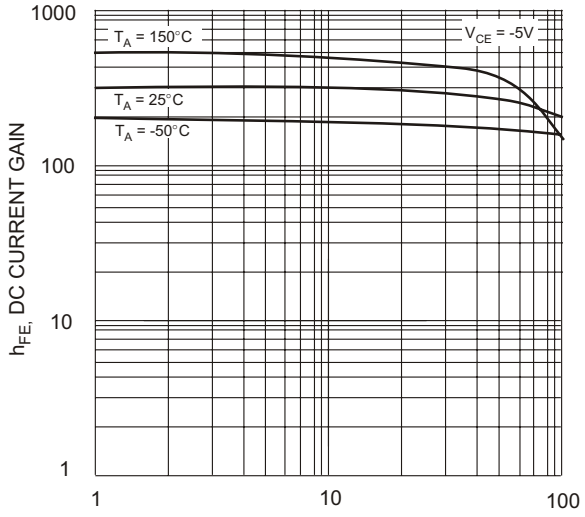


Fig. 2, DC Current Gain vs Collector Current

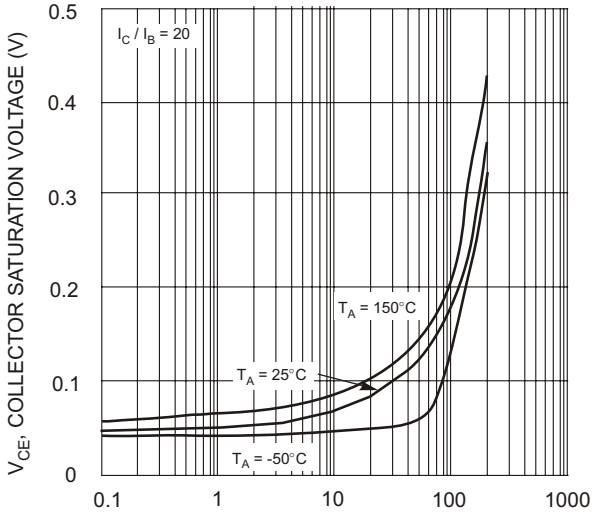


Fig. 3, Collector Saturation Voltage vs Collector Current

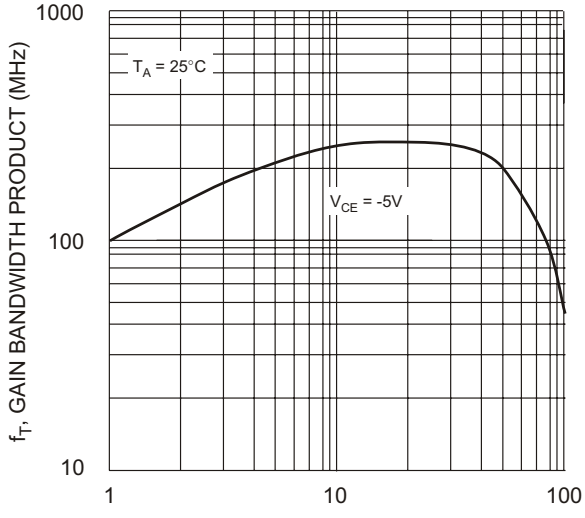


Fig. 4, Gain Bandwidth Product vs Collector Current